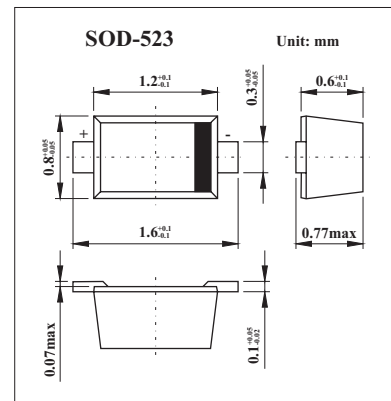


1PS79SB31

■ Features

- Very Low forward voltage
- Guard ring protected
- Ultra small plastic SMD package.



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Conditions	Min	Max	Unit
continuous reverse voltage	V _R			30	V
continuous forward current	I _F			200	mA
repetitive peak forward current	I _{FSM}	t _p ≤ 1s; δ ≤ 0.5		300	mA
non-repetitive peak forward current	I _{FSM}	t = 8.3 ms half sinewave; JEDEC method		1000	mA
storage temperature	T _{stg}		-65	+150	°C
junction temperature	T _j			125	°C
operating ambient temperature	T _{amb}		-65	+125	°C

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Conditions	Typ	Max	Unit
forward voltage	V _F	I _F = 0.1 mA	130	190	mV
		I _F = 1 mA	190	250	
		I _F = 10 mA	255	300	
		I _F = 100 mA	355	410	
		I _F = 200 mA	420	500	
capacitance reverse current	I _R	V _R = 10 V, note 1;	2.5	30	μA
diodes capacitance	C _d	V _R = 1 V, f = 1 MHz;	20	25	pF

Note

1. Pulse test: pulse t_p = 300 μs, δ = 0.02.

■ Marking

Marking	G3
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